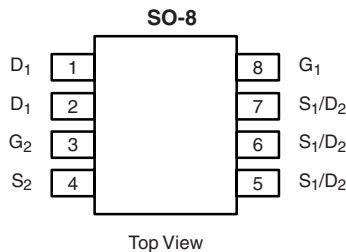


Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

PRODUCT SUMMARY				
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^a	Q _g (Typ.)
Channel-1	30	0.016 at V _{GS} = 10 V	10.7	8
		0.024 at V _{GS} = 4.5 V	8.6	
Channel-2	30	0.015 at V _{GS} = 10 V	11.3	19
		0.017 at V _{GS} = 4.5 V	10.6	

SCHOTTKY PRODUCT SUMMARY		
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)
30	0.43 V at 2.0 A	2.0



Ordering Information: Si4388DY-T1-E3 (Lead (Pb)-free)
Si4388DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

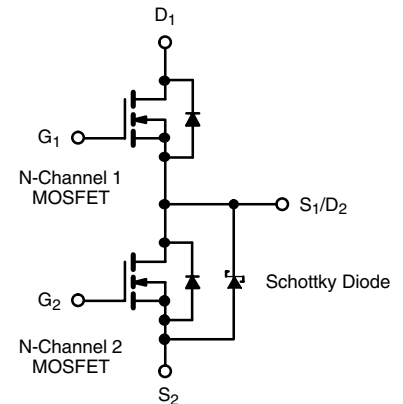
- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- CCFL Inverter
- Notebook Logic DC/DC



RoHS
COMPLIANT
HALOGEN
FREE
Available



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Channel-1	Channel-2	Unit
Drain-Source Voltage	V _{DS}	30	30	V
Gate-Source Voltage	V _{GS}	± 20	± 12	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	10.7	11.3
		T _C = 70 °C	8.5	- 9
		T _A = 25 °C	8.1 ^{b, c}	8.6 ^{b, c}
		T _A = 70 °C	6.4 ^{b, c}	6.9 ^{b, c}
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	40	40	A
Source-Drain Current Diode Current	I _S	T _C = 25 °C	3.0	
		T _A = 25 °C	1.7 ^{b, c}	1.8 ^{b, c}
Pulsed Source-Drain Current	I _{SM}	40	40	mJ
Single Pulse Avalanche Current	I _{AS}	15	20	
Single Pulse Avalanche Energy	E _{AS}	11.2	20	
Maximum Power Dissipation	P _D	T _C = 25 °C	3.3	3.5
		T _C = 70 °C	2.1	2.2
		T _A = 25 °C	1.9 ^{b, c}	2.2 ^{b, c}
		T _A = 70 °C	1.2 ^{b, c}	1.3 ^{b, c}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Channel-1		Channel-2		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 10 s	R _{thJA}	54	65	47	60	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	32	38	30	35	

Notes:

- Based on T_C = 25 °C.
- Surface Mounted on 1" x 1" FR4 board.
- t = 10 s.
- Maximum under Steady State conditions is 112 °C/W (Channel-1) and 107 °C/W (Channel-2).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	Ch-1	30		V	
		$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	Ch-2	30			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1	27			
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250\text{ }\mu\text{A}$	Ch-1	-6			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	Ch-1	1	3		
		$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	Ch-2	0.6	1.6		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	Ch-1		100	μA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	Ch-2		100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-1		0.001	mA	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	Ch-2	0.22	1		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$	Ch-1		0.025		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 100\text{ }^\circ\text{C}$	Ch-2	12	100		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-1	20		A	
		$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	Ch-2	20			
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-1		0.013	0.016	Ω
		$V_{GS} = 10\text{ V}, I_D = 8\text{ A}$	Ch-2		0.0125	0.015	
		$V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		0.017	0.024	
		$V_{GS} = 5\text{ V}, I_D = 5\text{ A}$	Ch-2		0.014	0.017	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-1		20	S	
		$V_{DS} = 15\text{ V}, I_D = 8\text{ A}$	Ch-2		38		
Dynamic^a							
Input Capacitance	C_{iss}	Channel-1 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1		946	pF	
			Ch-2		2230		
Output Capacitance	C_{oss}		Channel-2 $V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	Ch-1			173
				Ch-2			350
Reverse Transfer Capacitance	C_{rss}	Ch-1			84		
		Ch-2			133		
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 5\text{ A}$	Ch-1		18	27	nC
			Ch-2		41	62	
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		8	12	
			Ch-2		19	29	
Gate-Source Charge	Q_{gs}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		2.55		
Ch-2			3.5				
Gate-Drain Charge	Q_{gd}	$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 5\text{ A}$	Ch-1		2.45		
			Ch-2		3.7		
Gate Resistance	R_g	$f = 1\text{ MHz}$	Ch-1		2.8	4.2	Ω
			Ch-2		1.8	2.7	



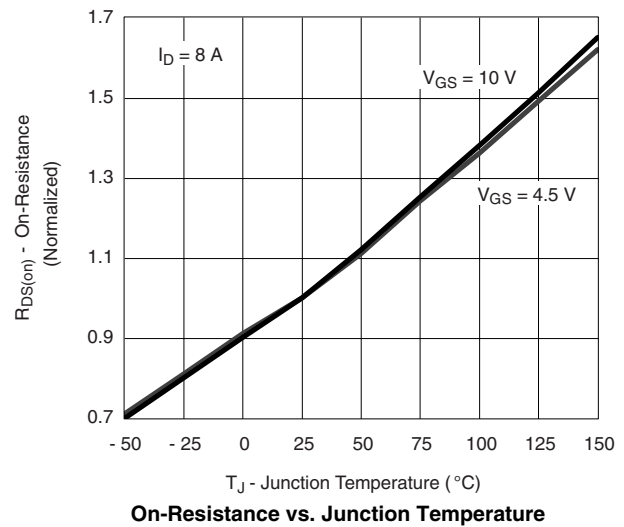
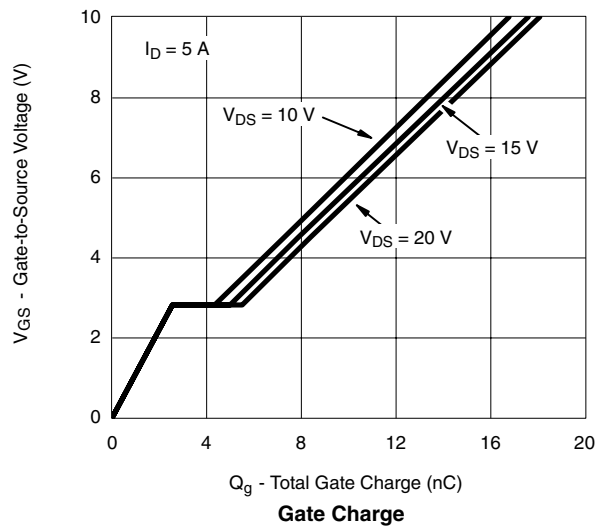
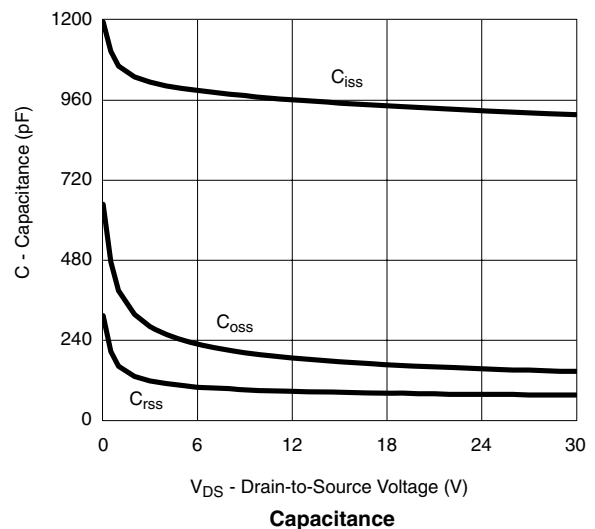
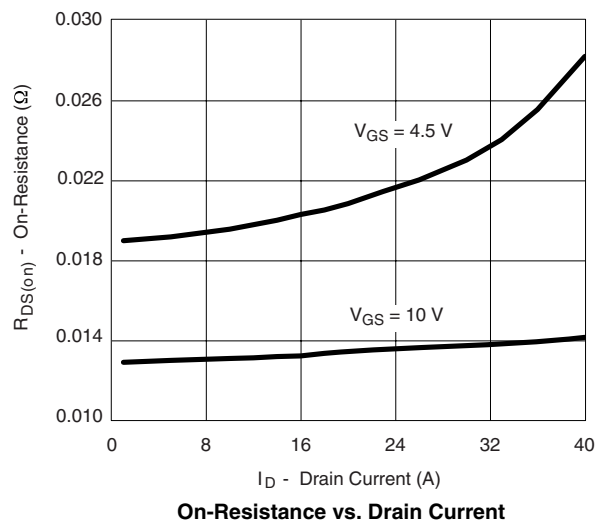
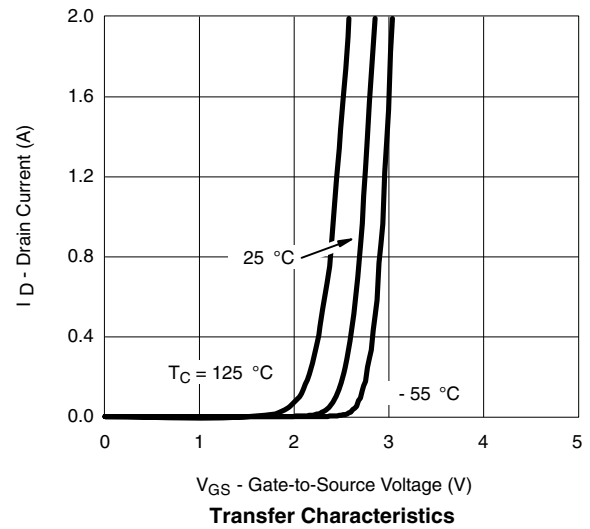
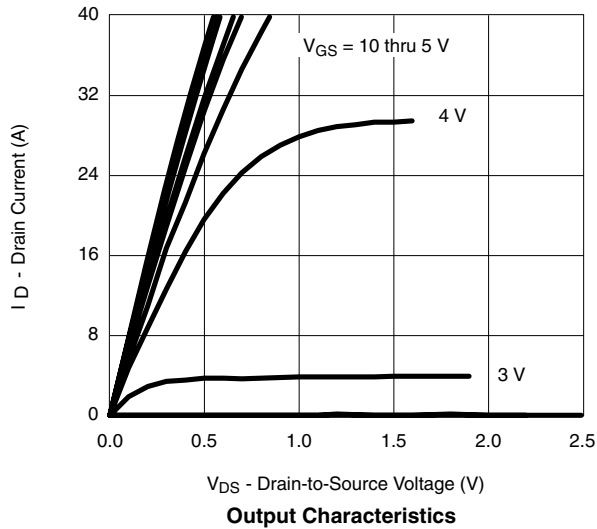
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit	
Dynamic^a							
Turn-On Delay Time	$t_{d(on)}$	Channel-1 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$ Channel-2 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\ \Omega$ Channel-1 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$ Channel-2 $V_{DD} = 15\text{ V}, R_L = 3\ \Omega$ $I_D \cong 5\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\ \Omega$	Ch-1		8	15	ns
			Ch-2		7	14	
Rise Time	t_r		Ch-1		10	15	
			Ch-2		10	15	
Turn-Off Delay Time	$t_{d(off)}$		Ch-1		20	30	
			Ch-2		40	60	
Fall Time	t_f		Ch-1		8	15	
			Ch-2		7	14	
Turn-On Delay Time	$t_{d(on)}$	Ch-1		13	20		
		Ch-2		14	22		
Rise Time	t_r	Ch-1		17	26		
		Ch-2		15	24		
Turn-Off Delay Time	$t_{d(off)}$	Ch-1		16	25		
		Ch-2		35	53		
Fall Time	t_f	Ch-1		8	15		
		Ch-2		7	14		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	Ch-1			3	A
			Ch-2			3.2	
Pulse Diode Forward Current ^a	I_{SM}		Ch-1			40	
			Ch-2			40	
Body Diode Voltage	V_{SD}	$I_S = 2\text{ A}$	Ch-1		0.8	1.1	V
			Ch-2		0.37	0.43	
Body Diode Reverse Recovery Time	t_{rr}	Channel-1 $I_F = 1.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ Channel-2 $I_F = 2.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	Ch-1		29	44	ns
			Ch-2		32	48	
Body Diode Reverse Recovery Charge	Q_{rr}		Ch-1		19	29	nC
			Ch-2		21	32	
Reverse Recovery Fall Time	t_a		Ch-1		12		ns
			Ch-2		13		
Reverse Recovery Rise Time	t_b		Ch-1		17		
			Ch-2		19		

Notes:

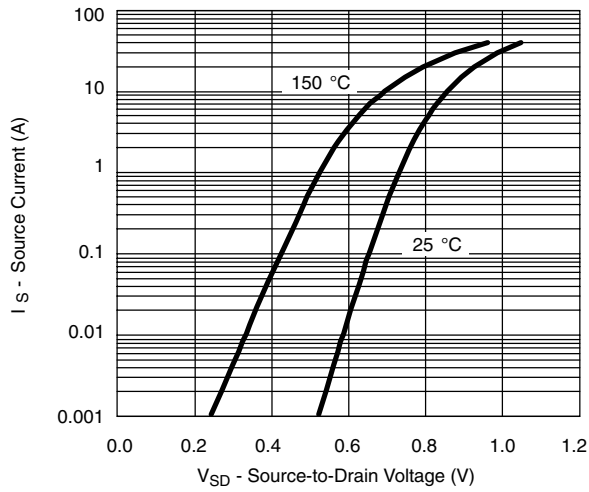
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

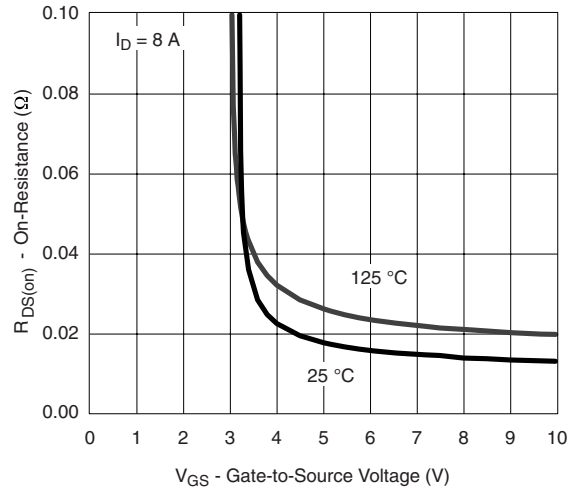
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



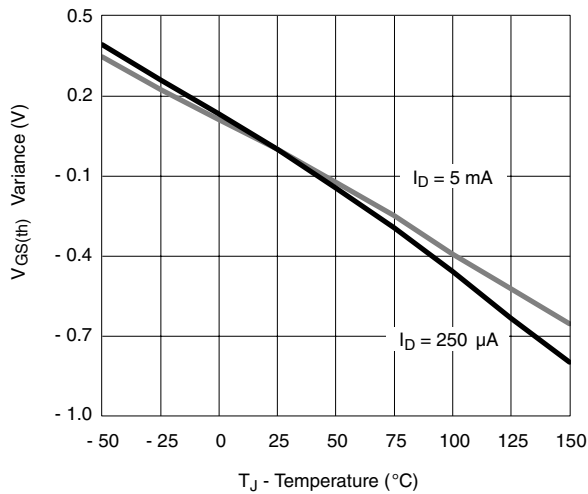
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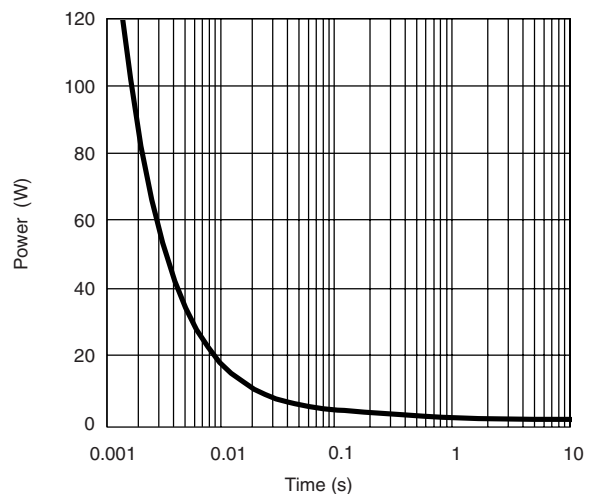
Source-Drain Diode Forward Voltage



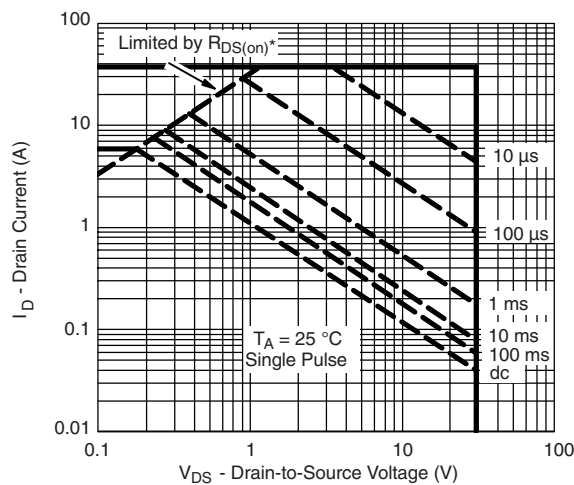
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

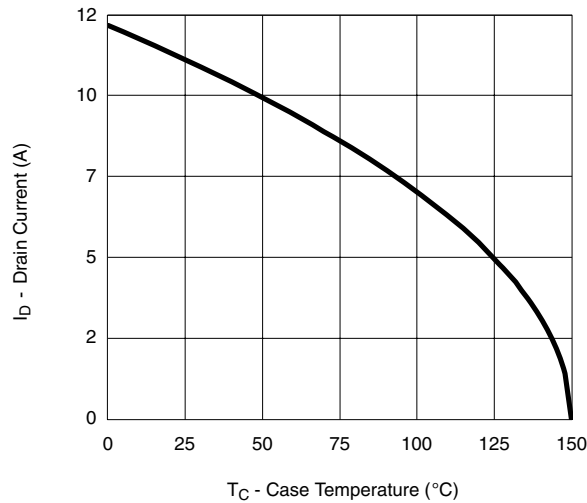


Single Pulse Power, Junction-to-Ambient

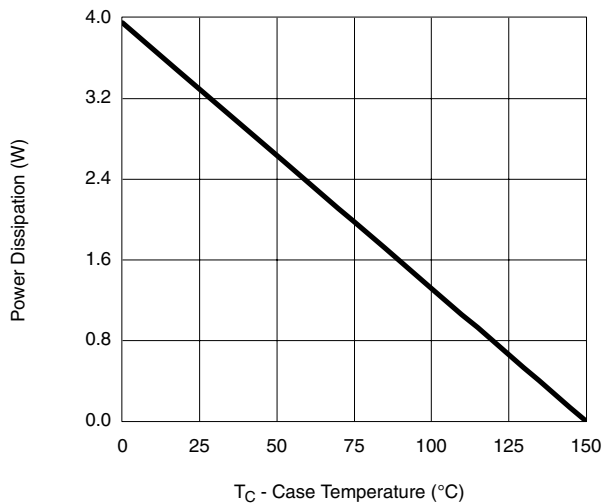


Safe Operating Area, Junction-to-Ambient

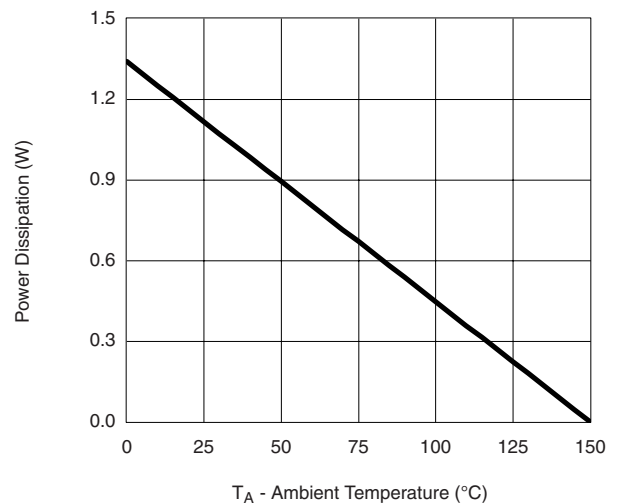
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



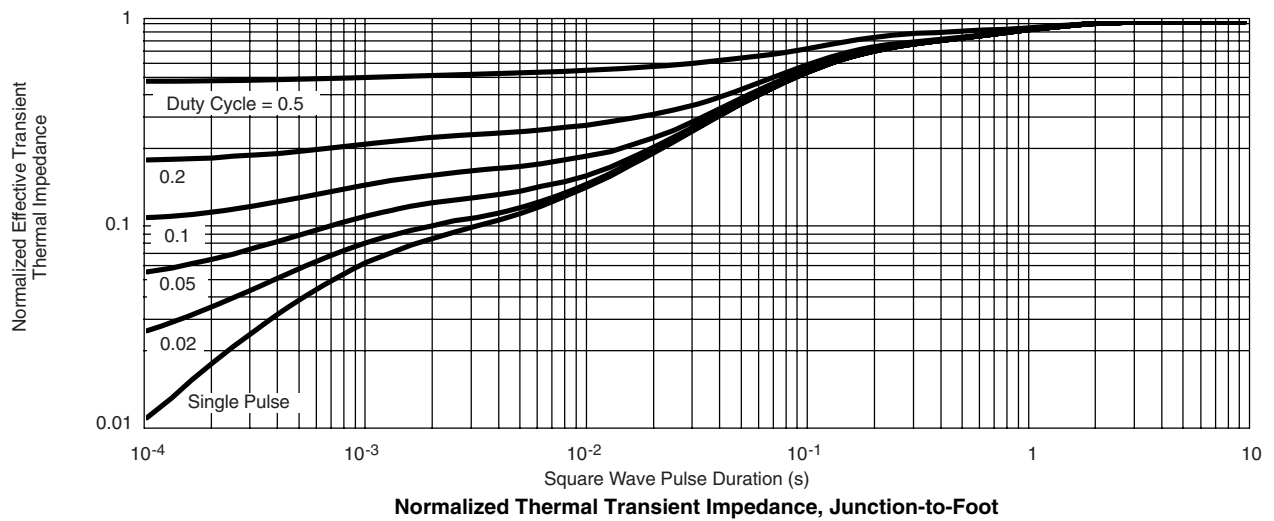
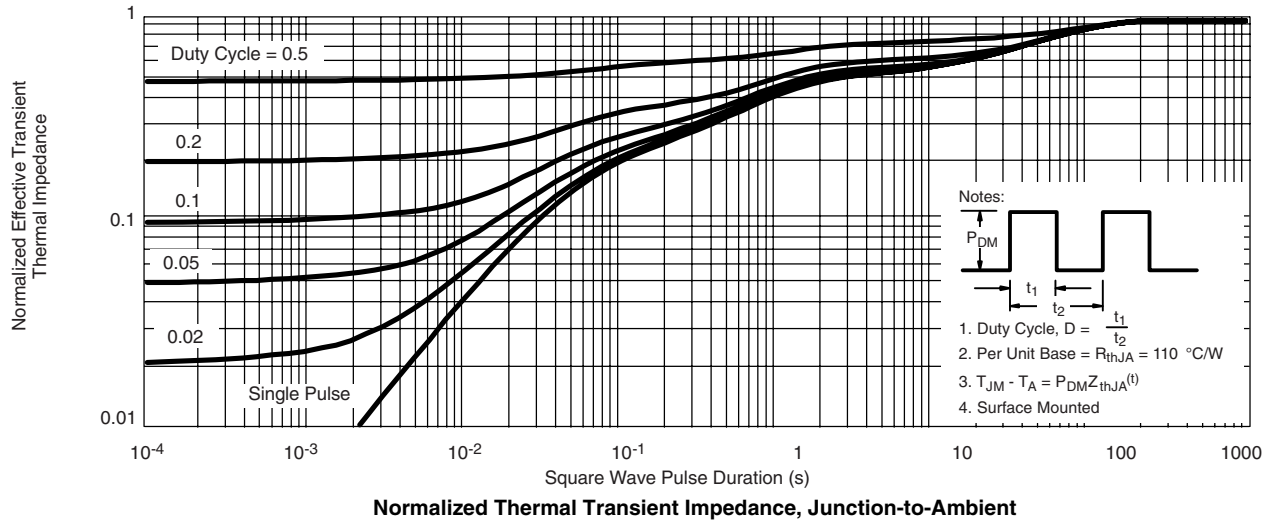
Power Derating, Junction-to-Foot



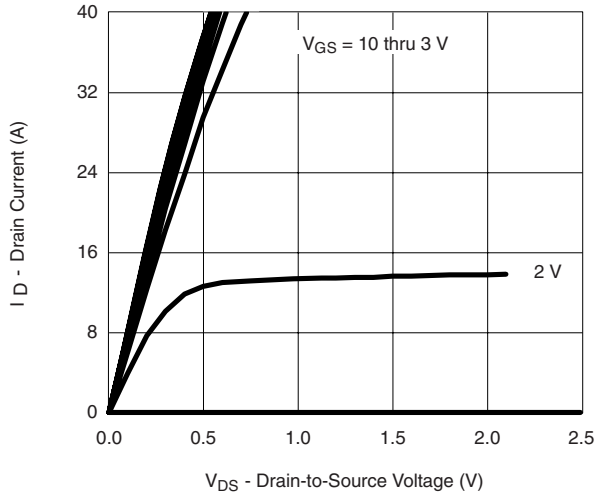
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

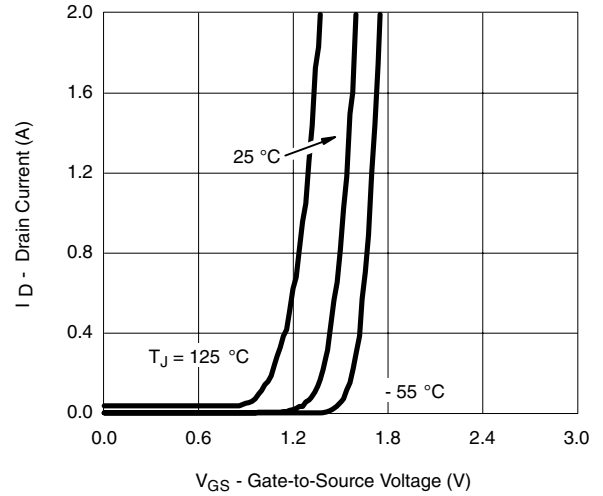
CHANNEL-1 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



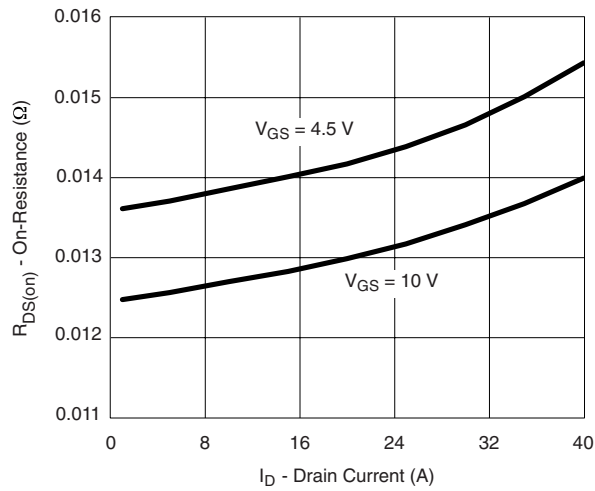
CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



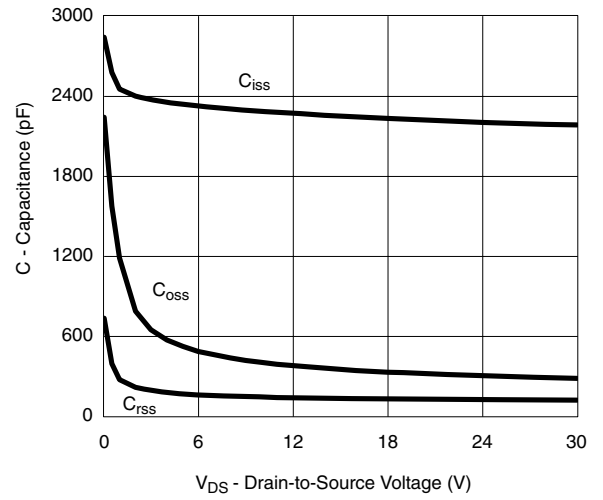
Output Characteristics



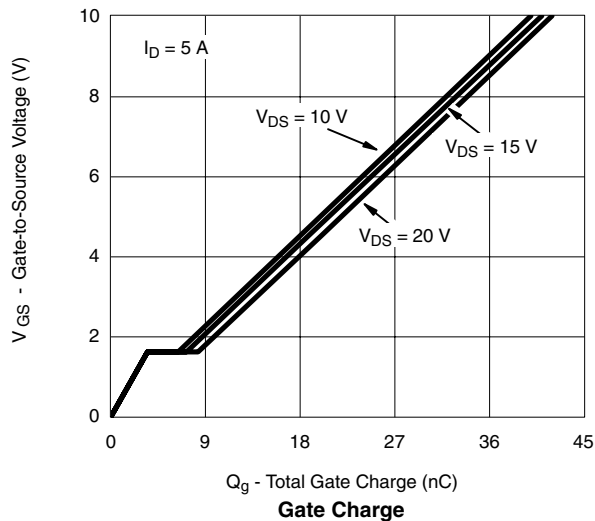
Transfer Characteristics



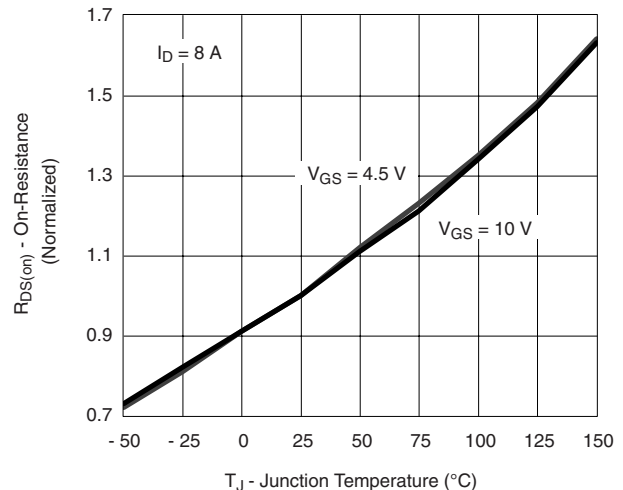
On-Resistance vs. Drain Current



Capacitance

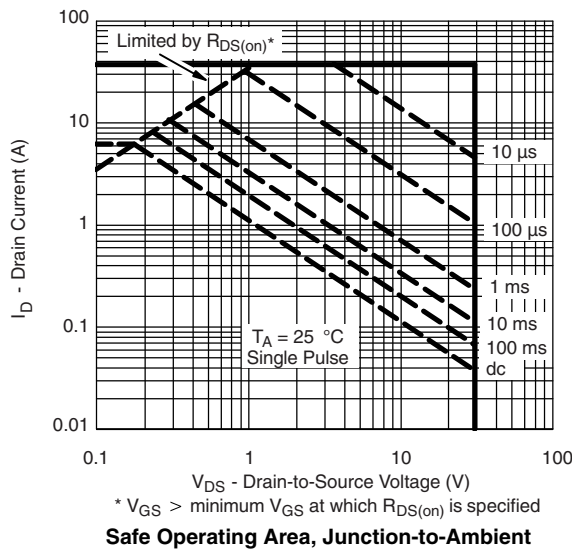
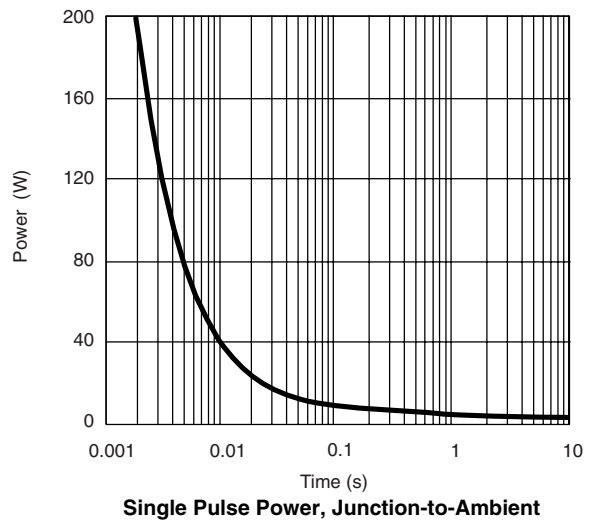
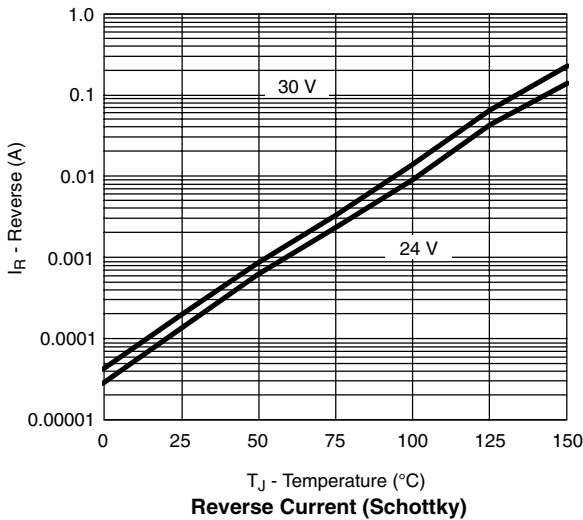
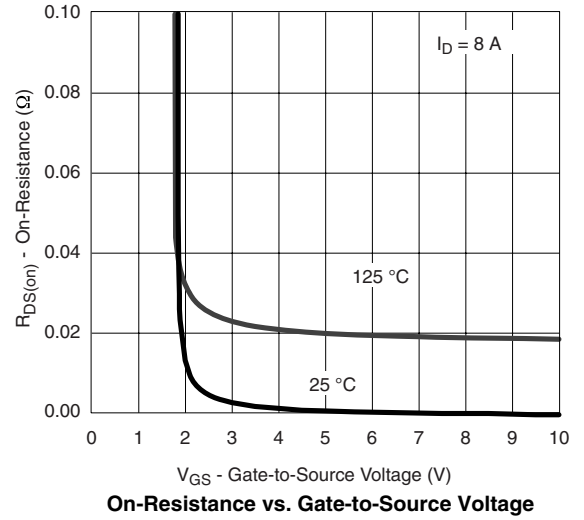
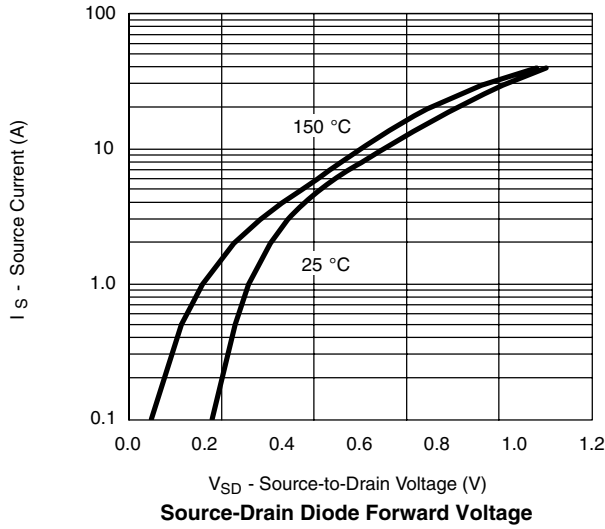


Gate Charge

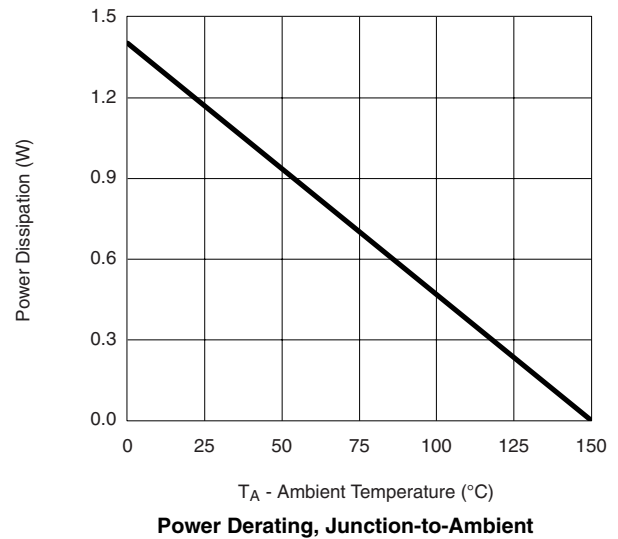
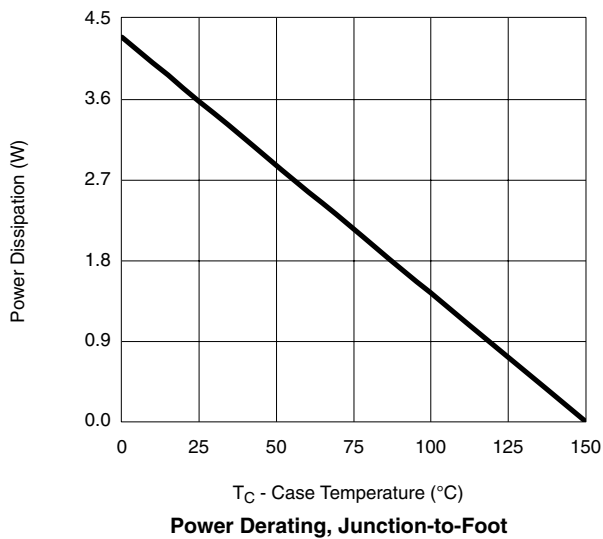
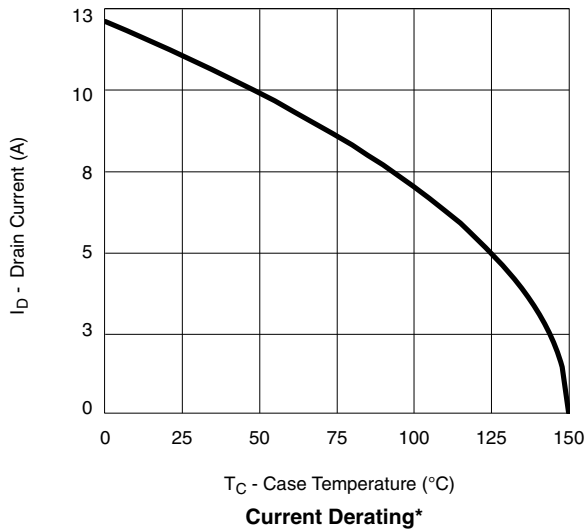


On-Resistance vs. Junction Temperature

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

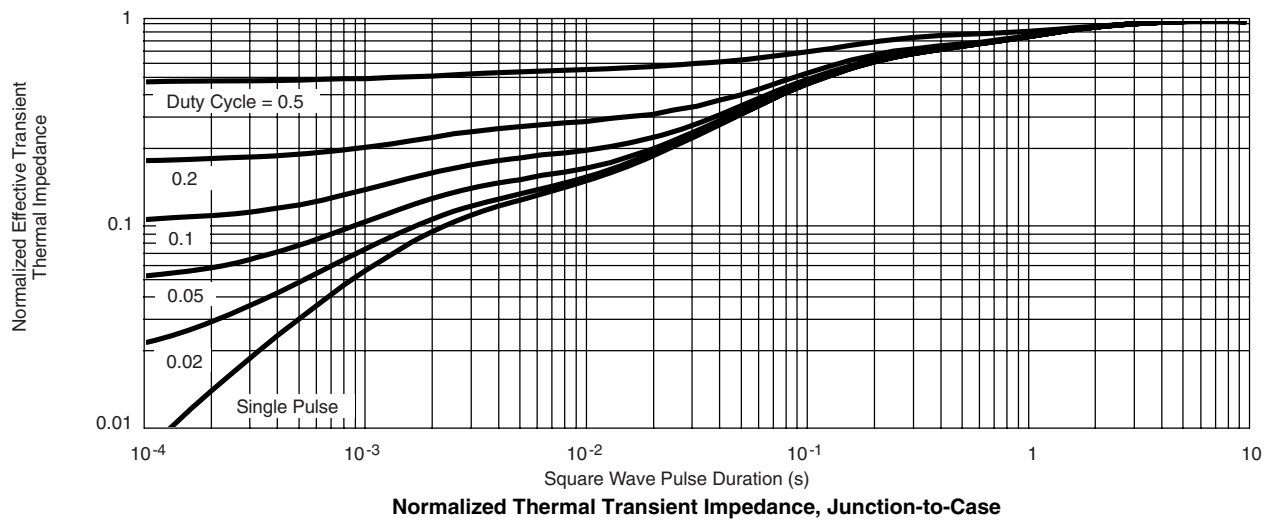
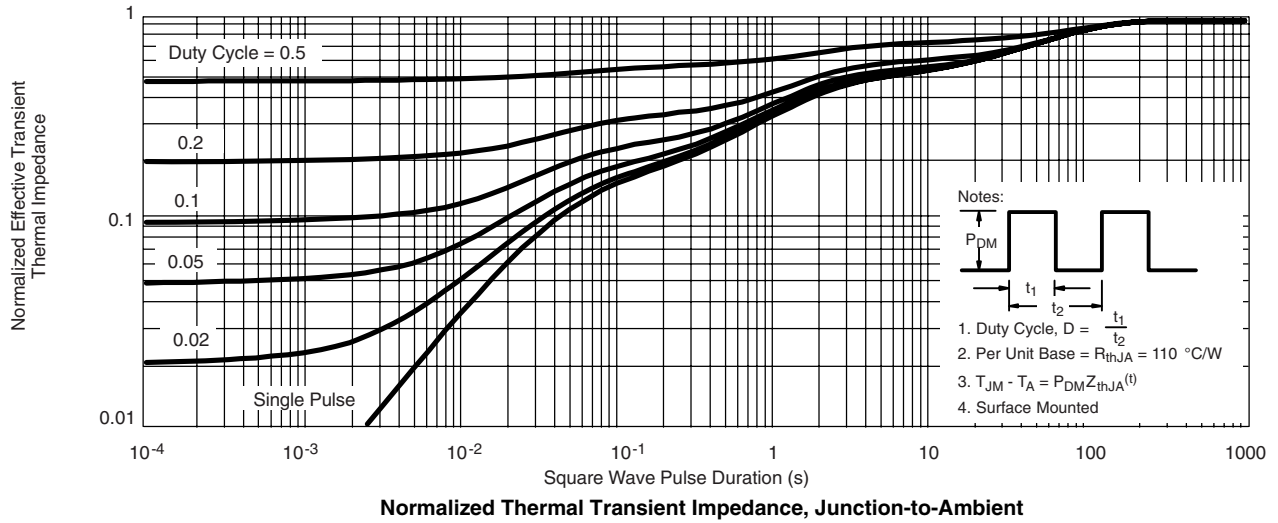


CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

CHANNEL-2 TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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